

**Features**

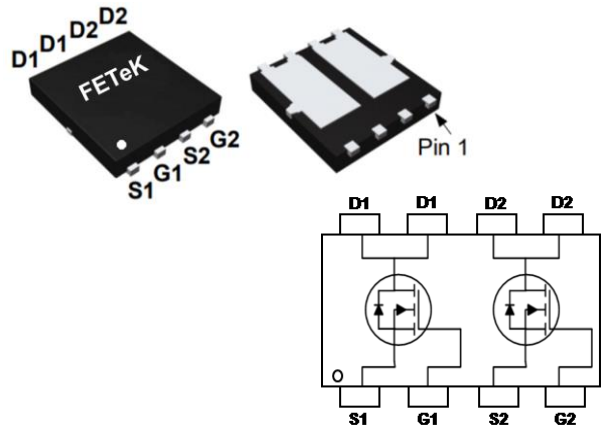
- Advanced Trench MOS Technology
- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available

**Product Summary**


BVDSS	RDSON	ID
100V	330mΩ	5A

**Application**

- Portable Equipment.
- Battery Powered Systems.
- Hard Switching and High-Speed Circuit.

**PRPAK5X6 Pin Configuration**

**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	5.0	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	3.1	A
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	1.5	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	1.2	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	11	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation <sup>3</sup>	17.8	W
$P_D @ T_A = 25^\circ C$	Total Power Dissipation <sup>3</sup>	1.5	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	---	80	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	7	$^\circ C/W$

**Electrical Characteristics ( $T_J=25\text{ }^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=3A$	---	290	330	m $\Omega$
		$V_{GS}=4.5V, I_D=3A$	---	300	360	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	---	3.0	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=80V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu A$
		$V_{DS}=80V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=5V, I_D=3A$	---	5.5	---	S
$R_g$	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	2.8	---	$\Omega$
$Q_g$	Total Gate Charge	$V_{DS}=80V, V_{GS}=10V, I_D=3A$	---	9.6	---	nC
$Q_{gs}$	Gate-Source Charge		---	1.83	---	
$Q_{gd}$	Gate-Drain Charge		---	1.85	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V, V_{GS}=10V, R_G=3.3\Omega, I_D=3A$	---	1.4	---	ns
$T_r$	Rise Time		---	30.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	11.2	---	
$T_f$	Fall Time		---	6	---	
$C_{iss}$	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	508	---	pF
$C_{oss}$	Output Capacitance		---	29	---	
$C_{riss}$	Reverse Transfer Capacitance		---	16.4	---	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,4</sup>	$V_G=V_D=0V, \text{Force Current}$	---	---	5	A
$I_{SM}$	Pulsed Source Current <sup>2,4</sup>		---	---	11	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
- 3.The power dissipation is limited by 150 $^\circ\text{C}$  junction temperature
- 4.The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications , should be limited by total power dissipation.

Typical Characteristics

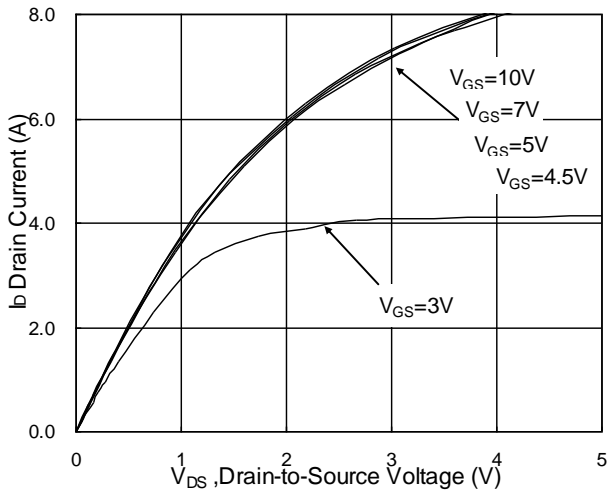


Fig.1 Typical Output Characteristics

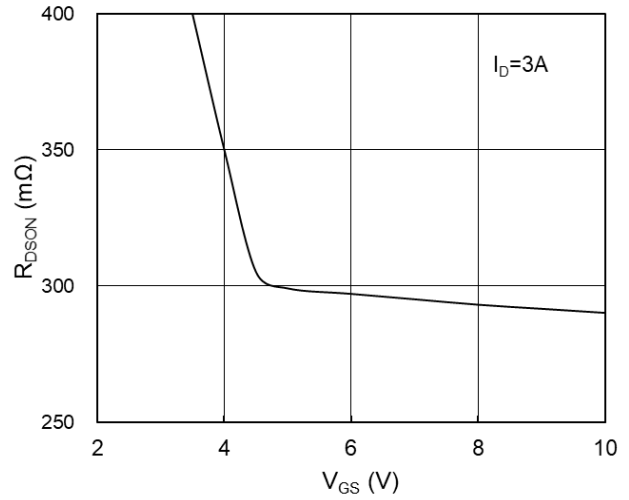


Fig.2 On-Resistance vs G-S Voltage

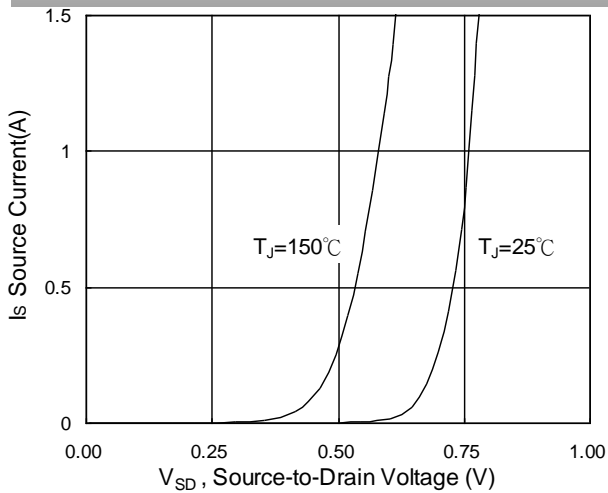


Fig.3 Source Drain Forward Characteristics

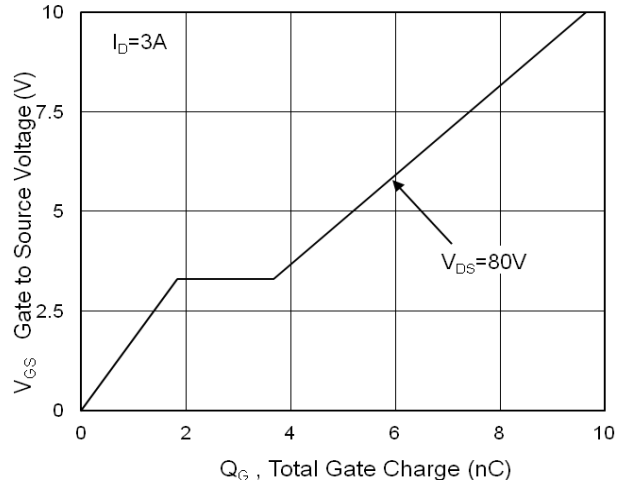


Fig.4 Gate-Charge Characteristics

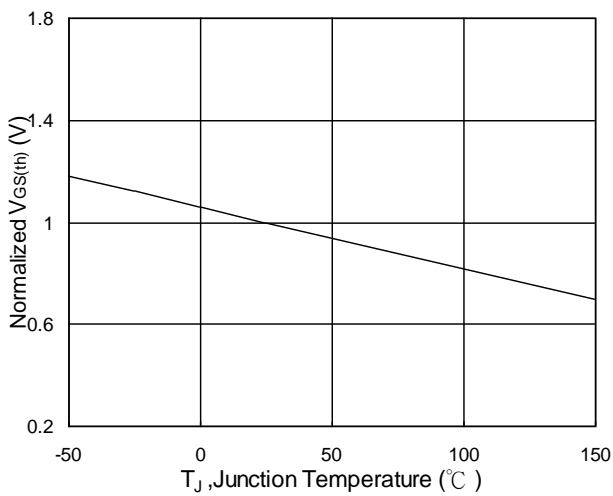


Fig.5 Normalized  $V_{GS(th)}$  vs  $T_J$

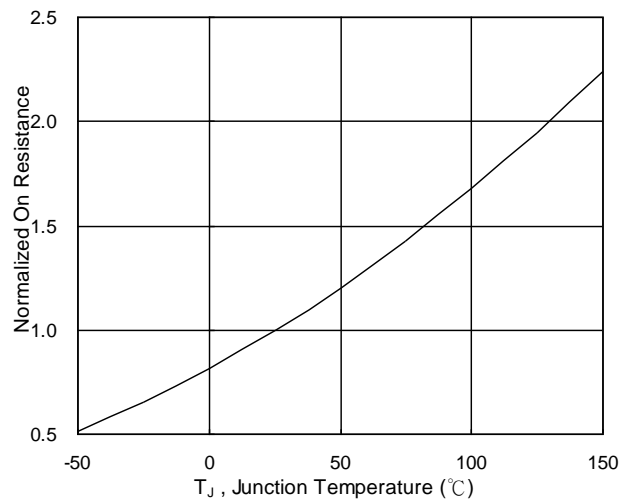


Fig.6 Normalized  $R_{DS(on)}$  vs  $T_J$

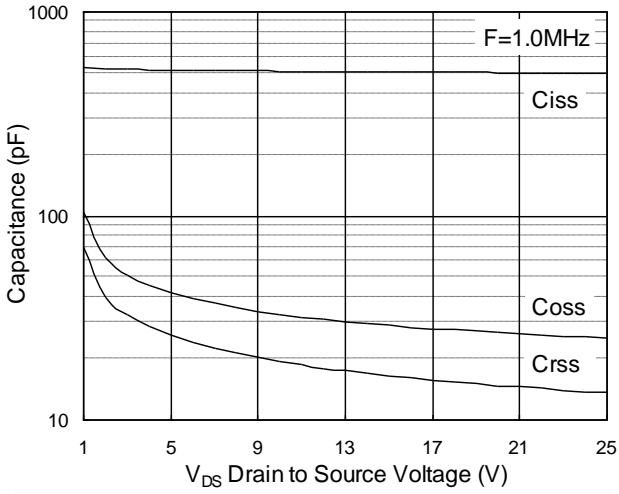


Fig.7 Capacitance

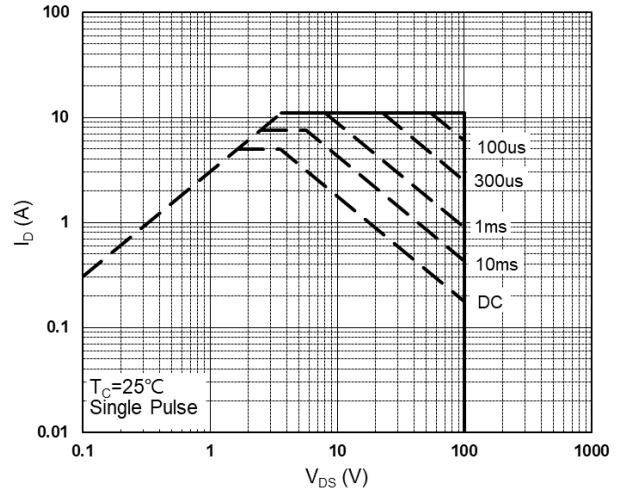


Fig.8 Safe Operating Area

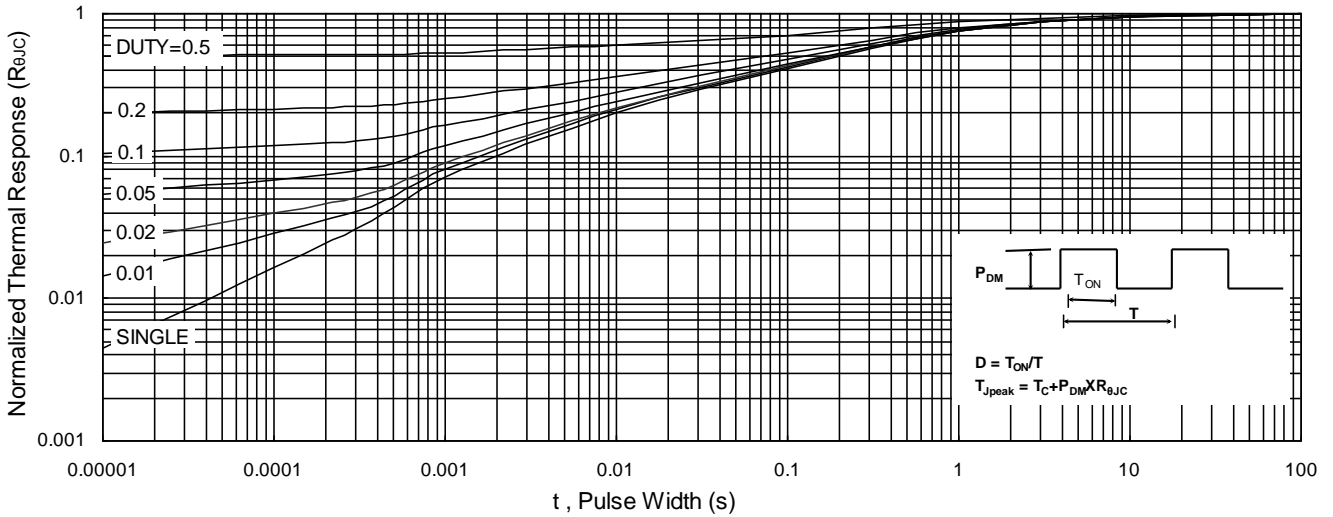


Fig.9 Normalized Maximum Transient Thermal Impedance

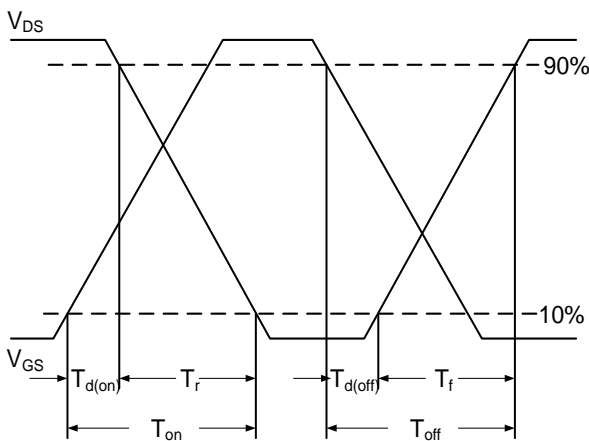


Fig.10 Switching Time Waveform

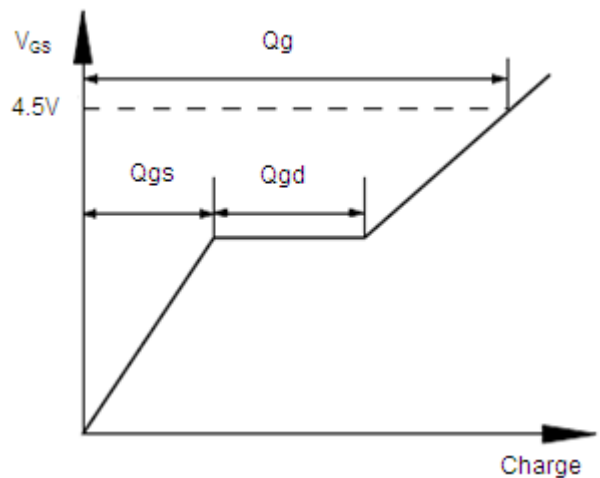


Fig.11 Gate Charge Waveform